

## SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

P-Channel Silicon MOSFET

# MCH3382 — Low Votage Drive Switching Device Applications

## **Features**

- ON-resistance RDS(on)1=152m $\Omega$  (typ.)
- · 1.2V drive
- · Halogen free compliance

## **Specifications**

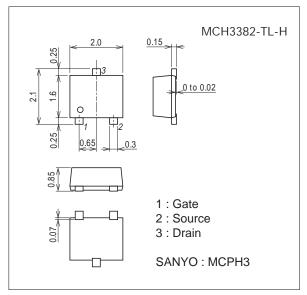
## Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		-12	V
Gate-to-Source Voltage	VGSS		±9	V
Drain Current (DC)	ID		-2	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	-8	Α
Allowable Power Dissipation	PD	When mounted on ceramic substrate (900mm <sup>2</sup> x0.8mm)	0.8	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

This product is designed to "ESD immunity < 200V\*", so please take care when handling.

## **Package Dimensions**

unit : mm (typ) 7019A-003

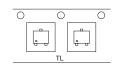


## **Product & Package Information**

• Package : MCPH3

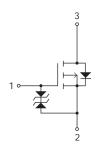
• JEITA, JEDEC : SC-70, SOT-323 • Minimum Packing Quantity : 3,000 pcs./reel

### Packing Type: TL Marking





### **Electrical Connection**

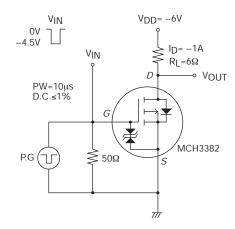


<sup>\*</sup> Machine Model

## Electrical Characteristics at Ta=25°C

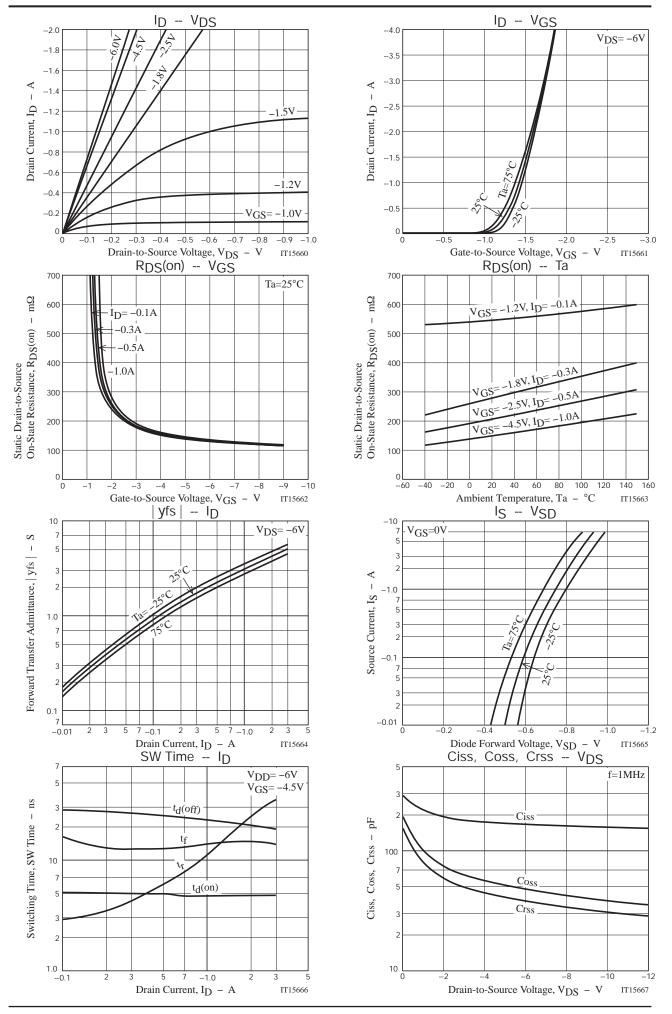
Parameter	Symbol	Conditions	Ratings			Unit	
Parameter	Symbol	Conditions	min	typ	max	Uill	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0V	-12			V	
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =-12V, V <sub>GS</sub> =0V			-10	μΑ	
Gate-to-Source Leakage Current	IGSS	V <sub>GS</sub> =±7.2V, V <sub>DS</sub> =0V			±10	μΑ	
Cutoff Voltage	V <sub>GS</sub> (off)	V <sub>DS</sub> =-6V, I <sub>D</sub> =-1mA	-0.3		-0.9	V	
Forward Transfer Admittance	yfs	V <sub>D</sub> S=-6V, I <sub>D</sub> =-1A		3		S	
	R <sub>DS</sub> (on)1	I <sub>D</sub> =-1A, V <sub>G</sub> S=-4.5V		152	198	mΩ	
Static Drain-to-Source On-State Resistance	R <sub>DS</sub> (on)2	I <sub>D</sub> =-0.5A, V <sub>G</sub> S=-2.5V		212	297	mΩ	
Static Drain-to-Source On-State Resistance	R <sub>DS</sub> (on)3	I <sub>D</sub> =-0.3A, V <sub>G</sub> S=-1.8V		286	429	mΩ	
	RDS(on)4	ID=-0.1A, VGS=-1.2V		520	1040	mΩ	
Input Capacitance	Ciss			170		pF	
Output Capacitance	Coss	V <sub>DS</sub> =-6V, f=1MHz		50		pF	
Reverse Transfer Capacitance	Crss			40		pF	
Turn-ON Delay Time	t <sub>d</sub> (on)			4.8		ns	
Rise Time	tr	Considered Took Circuit		11		ns	
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit.		23		ns	
Fall Time	t <sub>f</sub>			14		ns	
Total Gate Charge	Qg			2.3		nC	
Gate-to-Source Charge	Qgs	V <sub>D</sub> S=-6V, V <sub>G</sub> S=-4.5V, I <sub>D</sub> =-2A		0.40		nC	
Gate-to-Drain "Miller" Charge	Qgd	]		0.46		nC	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =-2A, V <sub>G</sub> S=0V		-0.85	-1.2	V	

## Switching Time Test Circuit

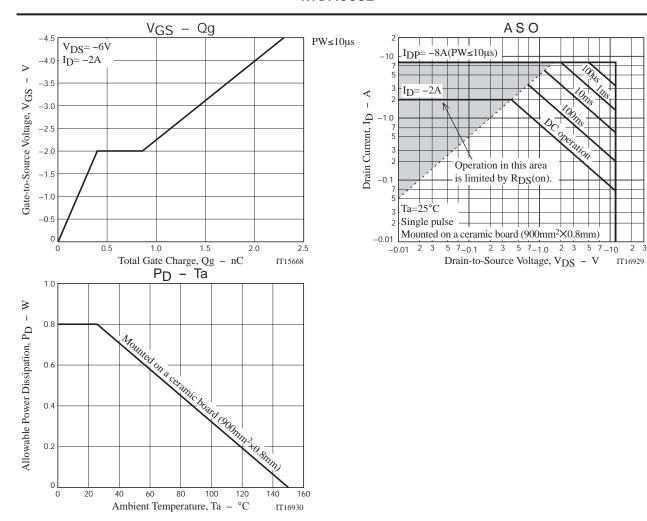


## **Ordering Information**

Device	Device Package		memo	
MCH3382-TL-H	MCPH3	3,000pcs./reel	Pb Free and Halogen Free	



ASO

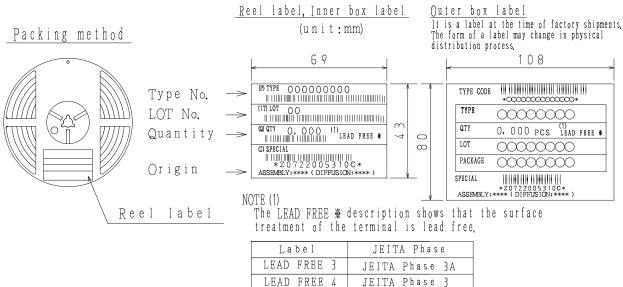


## **Taping Specification**

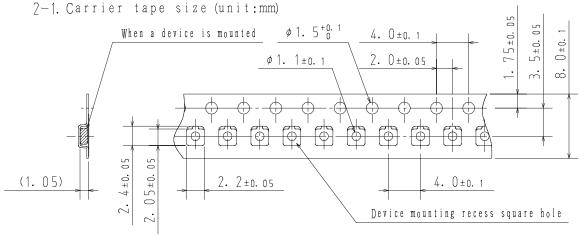
#### MCH3382-TL-H

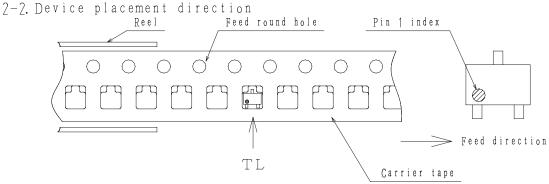
## 1. Packing Format

Packag	e Name	Carrier Tape	Maximun Number of devices contained (pcs)			Packing format		
		Туре	Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)	
MCI	РНЗ	мсрн3	3, 000	15, 000	90,000	5 reels contained	6 inner boxes contained	
	_					Dimensions:mm (external)	Dimensions:mm (external)	
						183×72×185	440×195×210	



## 2. Taping configuration

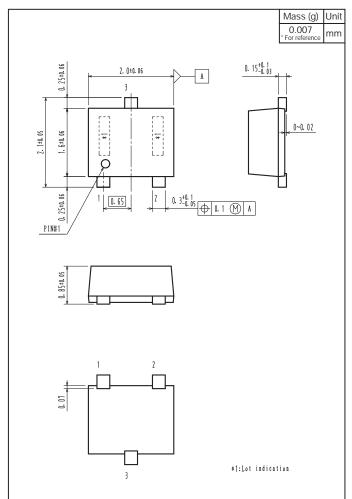




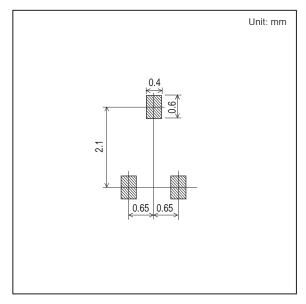
Those with pin 1 index on the feed hole side·····TL

## **Outline Drawing**

## MCH3382-TL-H



## Land Pattern Example



Note on usage: Since the MCH3382 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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